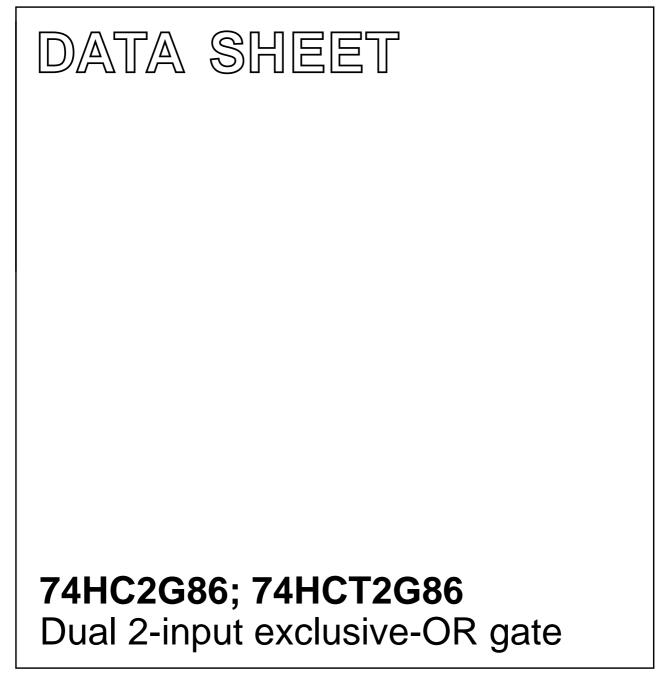
INTEGRATED CIRCUITS



Product specification

2002 Jul 17



FEATURES

- Wide supply voltage range from 2.0 to 6.0 V
- Symmetrical output impedance
- High noise immunity
- · Low power dissipation
- Balanced propagation delays
- Very small 8 pins package
- Output capability: standard.

QUICK REFERENCE DATA

 $GND = 0 \text{ V}; \text{ } T_{amb} = 25 \text{ }^{\circ}\text{C}; \text{ } t_r = t_f \leq 6.0 \text{ ns}.$

DESCRIPTION

The 74HC2G/HCT2G86 is a high-speed Si-gate CMOS device.

74HC2G86; 74HCT2G86

The 74HC2G/HCT2G86 provides dual 2-input exclusive-OR gate.

| SYMBOL | PARAMETER | CONDITIONS | ТҮР | UNIT | | |
|------------------------------------|--|---|--------|---------|------|--|
| STIVIDOL | FARAMETER | CONDITIONS | HC2G86 | HCT2G86 | UNIT | |
| t _{PHL} /t _{PLH} | propagation delay nA to nY | $C_L = 50 \text{ pF}; V_{CC} = 4.5 \text{ V}$ | 11 | 11 | ns | |
| CI | input capacitance | | 1.5 | 1.5 | pF | |
| C _{PD} | power dissipation capacitance per gate | notes 1 and 2 | 10 | 9 | pF | |

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total switching outputs;

 $\Sigma \ (C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

2. For HC1G the condition is V_I = GND to V_{CC} . For HCT1G the condition is V_I = GND to V_{CC} – 1.5 V.

FUNCTION TABLE

See note 1.

| INPUTS | INPUTS | OUTPUTS |
|--------|--------|---------|
| nA | nA | nY |
| L | L | L |
| L | Н | Н |
| Н | L | Н |
| Н | Н | L |

Note

1. H = HIGH voltage level;

L = LOW voltage level.

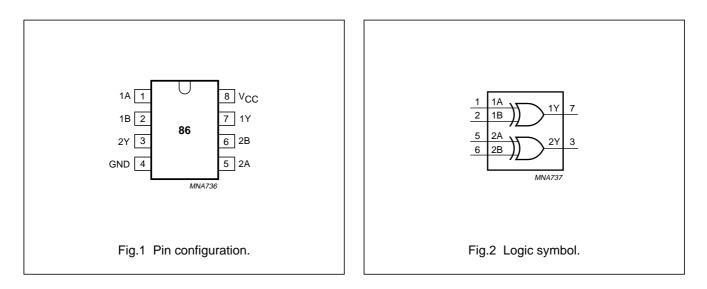
74HC2G86; 74HCT2G86

ORDERING INFORMATION

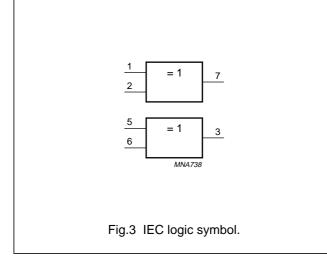
| | PACKAGES | | | | | | | | | | |
|-------------|-------------------|------|---------|----------|----------|---------|--|--|--|--|--|
| | TEMPERATURE RANGE | PINS | PACKAGE | MATERIAL | CODE | MARKING | | | | | |
| 74HC2G86DP | –40 to +125 °C | 8 | TSSOP-8 | plastic | SOT505-2 | H86 | | | | | |
| 74HCT2G86DP | –40 to +125 °C | 8 | TSSOP-8 | plastic | SOT505-2 | T86 | | | | | |

PINNING

| PIN | SYMBOL | DESCRIPTION |
|-----|-----------------|----------------|
| 1 | 1A | data input 1A |
| 2 | 1B | data input 1B |
| 3 | 2Y | data output 2Y |
| 4 | GND | ground (0 V) |
| 5 | 2A | data input 2A |
| 6 | 2B | data input 2B |
| 7 | 1Y | data output 1Y |
| 8 | V _{CC} | supply voltage |



74HC2G86; 74HCT2G86



RECOMMENDED OPERATING CONDITIONS

| Fig.4 Logic diagram (one driver). |
|-----------------------------------|

| SYMBOL | PARAMETER | CONDITIONS | 74HC2G86 | | | 74 | | | |
|---------------------------------|----------------------------------|--|----------|------|-----------------|------|------|-----------------|----|
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. | |
| V _{CC} | supply voltage | | 2.0 | 5.0 | 6.0 | 4.5 | 5.0 | 5.5 | V |
| VI | input voltage | | 0 | - | V _{CC} | 0 | - | V _{CC} | V |
| Vo | output voltage | | 0 | - | V _{CC} | 0 | - | V _{CC} | V |
| T _{amb} | operating ambient temperature | see DC and AC characteristics per device | -40 | +25 | +125 | -40 | +25 | +125 | °C |
| t _r , t _f | input rise and fall times | V _{CC} = 2.0 V | _ | - | 1000 | _ | - | _ | ns |
| | | V _{CC} = 4.5 V | _ | 6.0 | 500 | - | 6.0 | 500 | ns |
| | | V _{CC} = 6.0 V | - | - | 400 | - | - | _ | ns |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|--------------------------------|--|------|------|------|
| V _{CC} | supply voltage | | -0.5 | +7.0 | V |
| I _{IK} | input diode current | $V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V; note 1 | _ | ±20 | mA |
| I _{OK} | output diode current | $V_{\rm O}$ < -0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V; note 1 | _ | ±20 | mA |
| lo | output source or sink current | –0.5 V < V _O < V _{CC} + 0.5 V; note 1 | - | 25 | mA |
| I _{CC} | V _{CC} or GND current | note 1 | _ | 50 | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| P _D | power dissipation per package | for temperature range from –40 to +125 °C; note 2 | _ | 300 | mW |

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. Above 110 $^\circ\text{C}$ the value of P_D derates linearly with 8 mW/K.

74HC2G86; 74HCT2G86

DC CHARACTERISTICS

Type 74HC2G86

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| | | TEST CONDIT | IONS | | | T, | _{amb} (°C | ;) | | | |
|-----------------|------------------------------|---|---------------------|------|------|------|--------------------|-------|-------|--------|----|
| SYMBOL | PARAMETER | 071150 | | | 25 | | -40 t | o +85 | -40 t | o +125 | |
| | | OTHER | V _{CC} (V) | MIN. | TYP. | MAX. | MIN. | MAX. | MIN. | MAX. | 1 |
| VIH | HIGH-level input | | 2.0 | 1.5 | 1.2 | - | 1.5 | _ | 1.5 | - | V |
| | voltage | | 4.5 | 3.15 | 2.4 | _ | 3.15 | _ | 3.15 | _ | V |
| | | | 6.0 | 4.2 | 3.2 | _ | 4.2 | _ | 4.2 | _ | V |
| V _{IL} | LOW-level input | | 2.0 | - | 0.8 | 0.5 | _ | 0.5 | - | 0.5 | V |
| | voltage | | 4.5 | - | 2.1 | 1.35 | - | 1.35 | - | 1.35 | V |
| | | | 6.0 | - | 2.8 | 1.8 | _ | 1.8 | - | 1.8 | V |
| V _{OH} | HIGH-level output voltage | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -20 \ \mu\text{A}$ | 2.0 | 1.9 | 2.0 | - | 1.9 | _ | 1.9 | - | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -20 \ \mu\text{A}$ | 4.5 | 4.4 | 4.5 | - | 4.4 | _ | 4.4 | - | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -20 \ \mu\text{A}$ | 6.0 | 5.9 | 6.0 | - | 5.9 | _ | 5.9 | - | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -4.0 \text{ mA}$ | 4.5 | 4.18 | 4.32 | - | 4.13 | _ | 3.7 | - | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -5.2 \text{ mA}$ | 6.0 | 5.68 | 5.81 | - | 5.63 | _ | 5.2 | - | V |
| V _{OL} | LOW-level output voltage | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 20 \ \mu\text{A}$ | 2.0 | - | 0 | 0.1 | _ | 0.1 | - | 0.1 | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 20 \ \mu\text{A}$ | 4.5 | - | 0 | 0.1 | _ | 0.1 | - | 0.1 | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 20 \ \mu\text{A}$ | 6.0 | _ | 0 | 0.1 | _ | 0.1 | - | 0.1 | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 4.0 \text{ mA}$ | 4.5 | - | 0.15 | 0.26 | _ | 0.33 | - | 0.4 | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 5.2 \text{ mA}$ | 6.0 | - | 0.16 | 0.26 | _ | 0.33 | - | 0.4 | V |
| ILI | input leakage current | $V_{I} = V_{CC}$ or GND | 6.0 | - | - | ±0.1 | _ | ±1.0 | - | ±1.0 | μA |
| I _{CC} | quiescent supply current | $V_{I} = V_{CC}$ or GND; $I_{O} = 0$ | 6.0 | - | - | 1.0 | _ | 10 | - | 20 | μA |

74HC2G86; 74HCT2G86

Type 74HCT2G86

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| | | TEST CONDITIONS | | T _{amb} (°C) | | | | | | | |
|-----------------|-------------------------------------|---|---------------------|-----------------------|------|------|------------|------|-------------|------|------|
| SYMBOL | PARAMETER | | | 25 | | | -40 to +85 | | -40 to +125 | | UNIT |
| | | OTHER | V _{CC} (V) | MIN. | TYP. | MAX. | MIN. | MAX. | MIN. | MAX. | |
| V _{IH} | HIGH-level input voltage | | 4.5 to 5.5 | 2.0 | 1.6 | - | 2.0 | - | 2.0 | - | V |
| V _{IL} | LOW-level input voltage | | 4.5 to 5.5 | - | 1.2 | 0.8 | - | 0.8 | - | 0.8 | V |
| V _{OH} | HIGH-level output voltage | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -20 \ \mu\text{A}$ | 4.5 | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -4.0 \text{ mA}$ | 4.5 | 4.18 | 4.32 | - | 4.13 | - | 3.7 | - | V |
| V _{OL} | LOW-level output voltage | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 20 \ \mu\text{A}$ | 4.5 | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | $V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 4.0 \text{ mA}$ | 4.5 | - | 0.15 | 0.26 | - | 0.33 | - | 0.4 | V |
| ILI | input leakage current | $V_I = V_{CC}$ or GND | 5.5 | _ | - | ±0.1 | - | ±1.0 | - | ±1.0 | μA |
| I _{CC} | quiescent supply current | $V_{I} = V_{CC} \text{ or } GND;$ $I_{O} = 0$ | 5.5 | _ | - | 1.0 | - | 10 | - | 20 | μA |
| ΔI_{CC} | additional supply current per input | $V_{I} = V_{CC} - 2.1 \text{ V};$ $I_{O} = 0$ | 4.5 to 5.5 | - | - | 300 | - | 375 | - | 410 | μA |

74HC2G86; 74HCT2G86

AC CHARACTERISTICS

Type 74HC2G86

GND = 0 V; $t_r = t_f \le 6.0$ ns; $C_L = 50$ pF.

| | | TEST CONDIT | IONS | | | Т | amb (°C | | | | |
|------------------------------------|-------------------|------------------|---------------------|------|------|------|---------|-------|-------------|------|------|
| SYMBOL | PARAMETER | WAVEFORMS | V _{cc} (V) | | 25 | | | o +85 | -40 to +125 | | UNIT |
| | | WAVEFORMS | | MIN. | TYP. | MAX. | MIN. | MAX. | MIN. | MAX. | |
| t _{PHL} /t _{PLH} | propagation delay | see Figs 5 and 6 | 2.0 | _ | 34 | 120 | _ | 150 | _ | 180 | ns |
| | nA, nB to nY | , nB to nY | 4.5 | - | 11 | 20 | _ | 25 | _ | 36 | ns |
| | | | 6.0 | - | 9 | 17 | _ | 21 | _ | 30 | ns |
| t _{THL} /t _{TLH} | output transition | see Figs 5 and 6 | 2.0 | - | 18 | 75 | _ | 95 | _ | 110 | ns |
| | time | | 4.5 | - | 6 | 15 | - | 19 | - | 22 | ns |
| | | | 6.0 | - | 5 | 13 | _ | 16 | _ | 20 | ns |

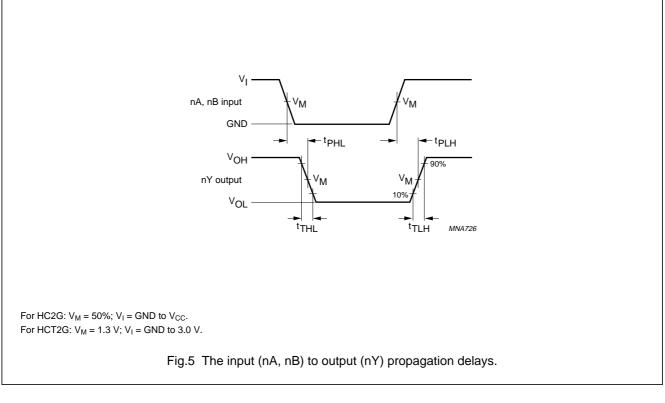
Type 74HCT2G86

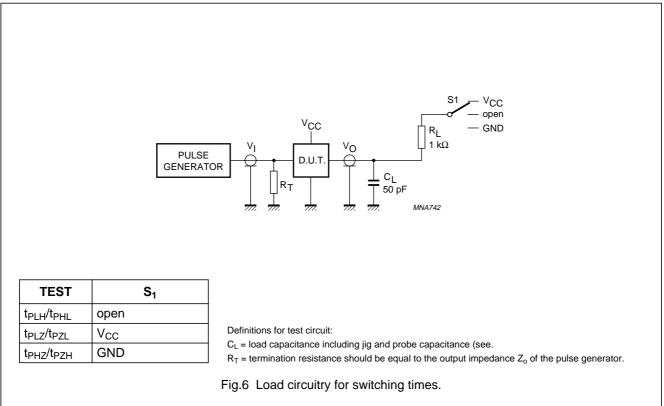
GND = 0 V; t_r = $t_f \leq$ 6.0 ns; C_L = 50 pF.

| | | TEST CONDIT | T _{amb} (°C) | | | | | | | | |
|------------------------------------|-----------------------------------|------------------|-----------------------|------|------|------|------------|------|-------------|------|------|
| SYMBOL | | | | 25 | | | -40 to +85 | | -40 to +125 | | UNIT |
| | | WAVEFORMS V | V _{CC} (V) | MIN. | TYP. | MAX. | MIN. | MAX. | MIN. | MAX. | |
| t _{PHL} /t _{PLH} | propagation delay nA, nB to nY | see Figs 5 and 6 | 4.5 | - | 11 | 19 | - | 23 | _ | 48 | ns |
| t _{THL} /t _{TLH} | output transition time | see Figs 5 and 6 | 4.5 | _ | 6 | 15 | _ | 19 | _ | 22 | ns |

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AC WAVEFORMS

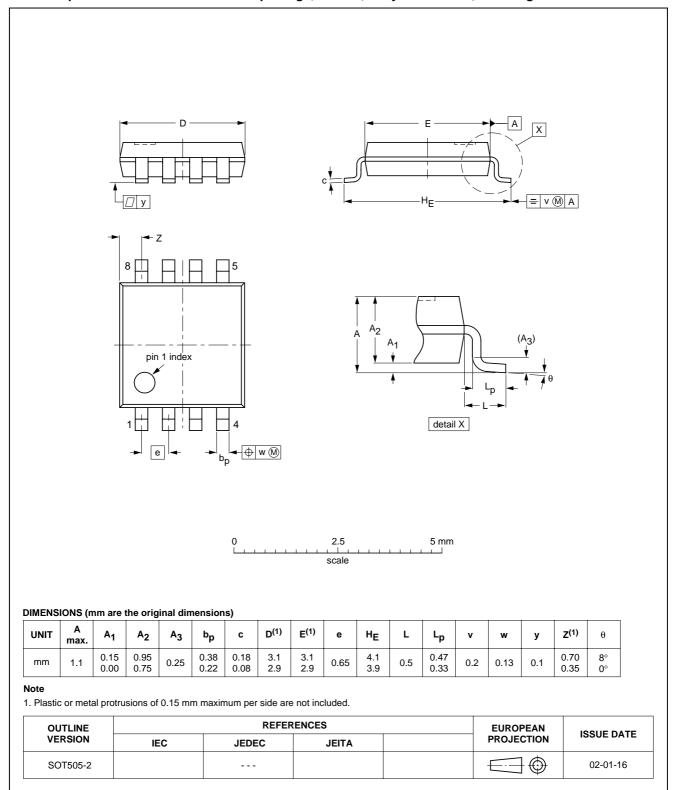




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PACKAGE OUTLINE

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



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SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^\circ\text{C}.$

74HC2G86; 74HCT2G86

Suitability of surface mount IC packages for wave and reflow soldering methods

| PACKAGE ⁽¹⁾ | SOLDERING METHOD | | | | |
|--|-----------------------------------|-----------------------|--|--|--|
| PACKAGE (*) | WAVE | REFLOW ⁽²⁾ | | | |
| BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA | not suitable | suitable | | | |
| HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS | not suitable ⁽³⁾ | suitable | | | |
| PLCC ⁽⁴⁾ , SO, SOJ | suitable | suitable | | | |
| LQFP, QFP, TQFP | not recommended ⁽⁴⁾⁽⁵⁾ | suitable | | | |
| SSOP, TSSOP, VSO | not recommended ⁽⁶⁾ | suitable | | | |

Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 6. Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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DATA SHEET STATUS

| DATA SHEET STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITIONS |
|----------------------------------|----------------------------------|--|
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| Preliminary data | Qualification | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product. |
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Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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